

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



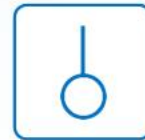
MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	AO4884
▶ Overseas	Part Number	AO4884
▶ Equivalent	Part Number	AO4884

EV is the abbreviation of name EVVO

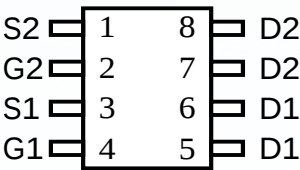
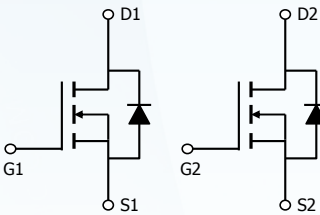
Dual N-Channel MOSFET

General Description

The AO4884 uses advanced trench technology to provide excellent $R_{DS(ON)}$ with low gate charge. This is an all purpose device that is suitable for use in a wide range of power conversion applications.

Product Summary

V_{DS}	40V
I_D (at $V_{GS}=10V$)	10A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 13mΩ
$R_{DS(ON)}$ (at $V_{GS} = 4.5V$)	< 16mΩ



Absolute Maximum Ratings $T_A=25^{\circ}C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	10	A
$T_A=25^{\circ}C$		8	
Pulsed Drain Current ^C	I_{DM}	50	
Avalanche Current ^C	I_{AS}, I_{AR}	35	A
Avalanche energy $L=0.1mH$ ^C	E_{AS}, E_{AR}	61	mJ
Power Dissipation ^B	P_D	2	W
$T_A=25^{\circ}C$		1.3	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	48	62.5	$^{\circ}C/W$
$t \leq 10s$				
Maximum Junction-to-Ambient ^{A D}	$R_{\theta JL}$	74	90	$^{\circ}C/W$
Steady-State				
Maximum Junction-to-Lead	$R_{\theta JL}$	32	40	$^{\circ}C/W$
Steady-State				

Dual N-Channel MOSFET

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	40			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=40\text{V}$, $V_{GS}=0\text{V}$			1	μA
		$T_J=55^\circ\text{C}$			5	
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1.2	1.5	2.5	V
$I_{D(ON)}$	On state drain current	$V_{GS}=10\text{V}$, $V_{DS}=5\text{V}$	50			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=10\text{A}$		11	13	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=10\text{A}$		12	16	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=10\text{A}$		50		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.7	1	V
I_S	Maximum Body-Diode Continuous Current				2.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=20\text{V}$, $f=1\text{MHz}$	1200	1500	1950	pF
C_{oss}	Output Capacitance		150	215	280	pF
C_{rss}	Reverse Transfer Capacitance		80	135	190	pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$	1.7	3.5	5.3	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=20\text{V}$, $I_D=10\text{A}$	22	27.2	33	nC
$Q_g(4.5\text{V})$	Total Gate Charge		10	13.6	16	nC
Q_{gs}	Gate Source Charge		3.6	4.5	5.4	nC
Q_{gd}	Gate Drain Charge		3.8	6.4	9	nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$, $V_{DS}=20\text{V}$, $R_L=2\Omega$, $R_{GEN}=3\Omega$		6.4		ns
t_r	Turn-On Rise Time			17.2		ns
$t_{D(off)}$	Turn-Off DelayTime			29.6		ns
t_f	Turn-Off Fall Time			16.8		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=10\text{A}$, $dI/dt=500\text{A}/\mu\text{s}$	9	13	17	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=10\text{A}$, $dI/dt=500\text{A}/\mu\text{s}$	25	35	45	nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on $T_{J(MAX)}=150^\circ\text{C}$, using $\leq 10\text{s}$ junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.

D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}=150^\circ\text{C}$. The SOA curve provides a single pulse rating.

Dual N-Channel MOSFET

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

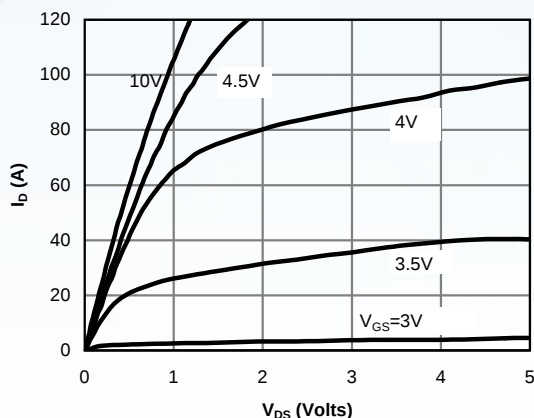


Fig 1: On-Region Characteristics (Note E)

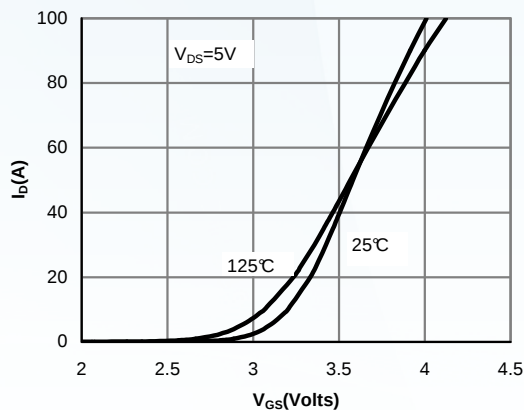


Figure 2: Transfer Characteristics (Note E)

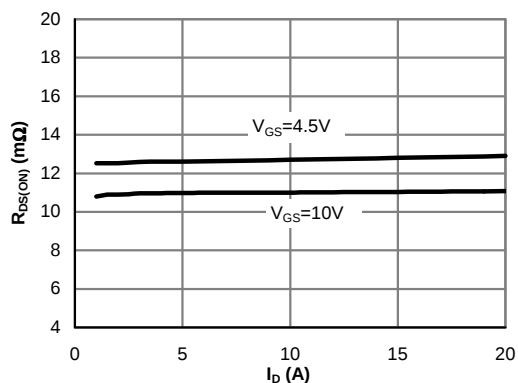


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

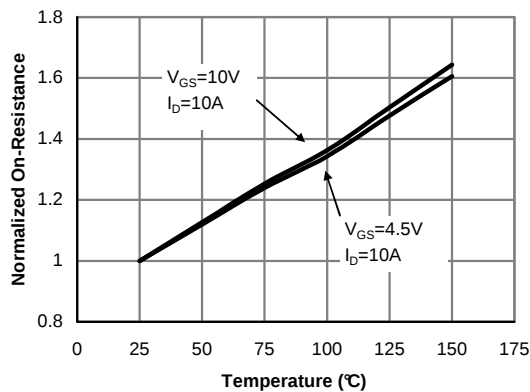


Figure 4: On-Resistance vs. Junction Temperature (Note E)

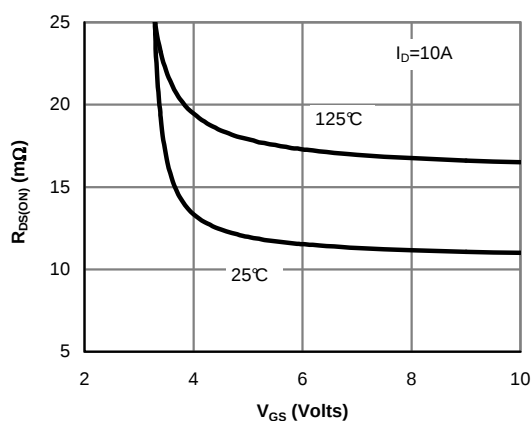


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

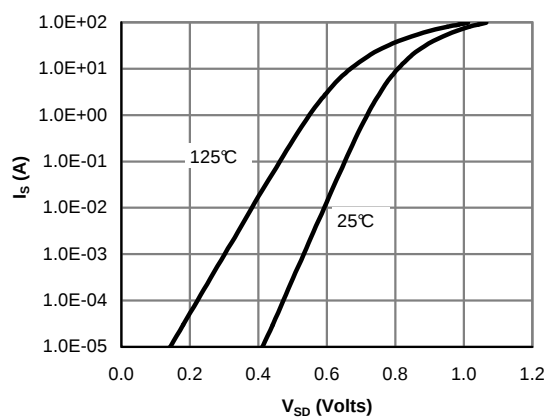


Figure 6: Body-Diode Characteristics (Note E)

Dual N-Channel MOSFET

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

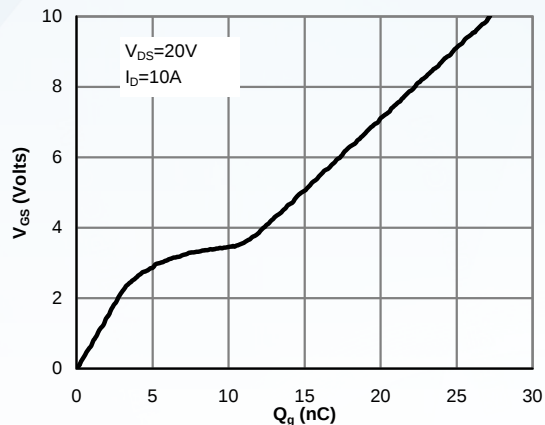


Figure 7: Gate-Charge Characteristics

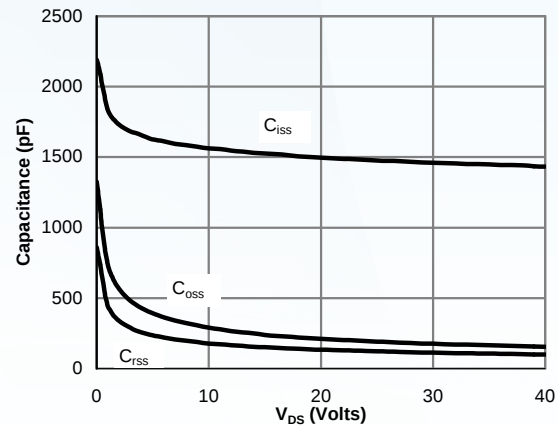


Figure 8: Capacitance Characteristics

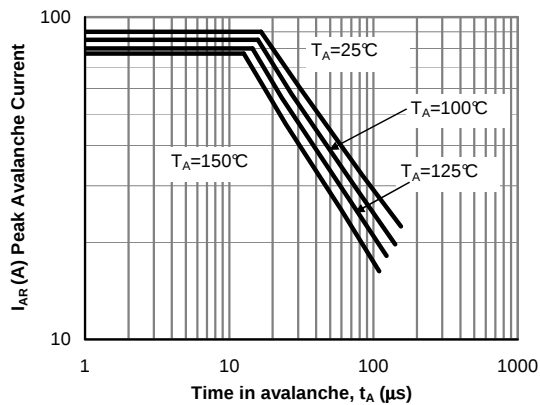


Figure 9: Single Pulse Avalanche capability (Note C)

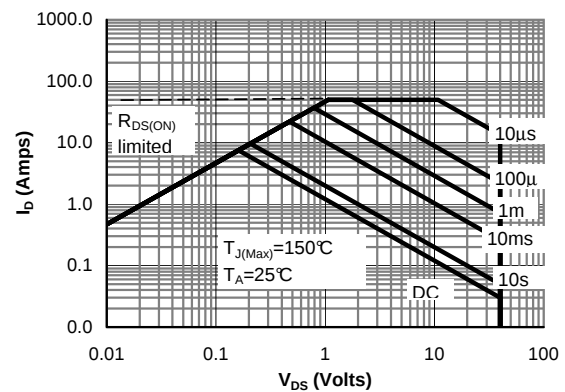


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

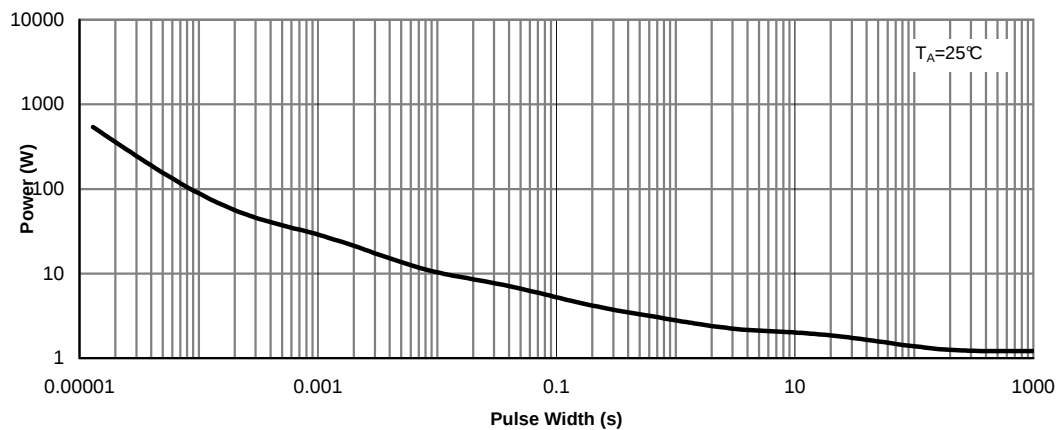


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

Dual N-Channel MOSFET

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

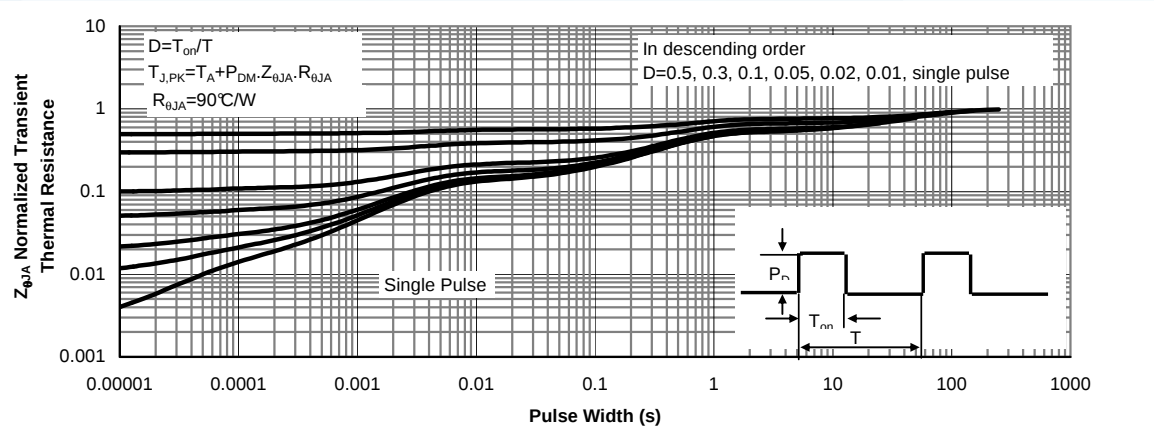
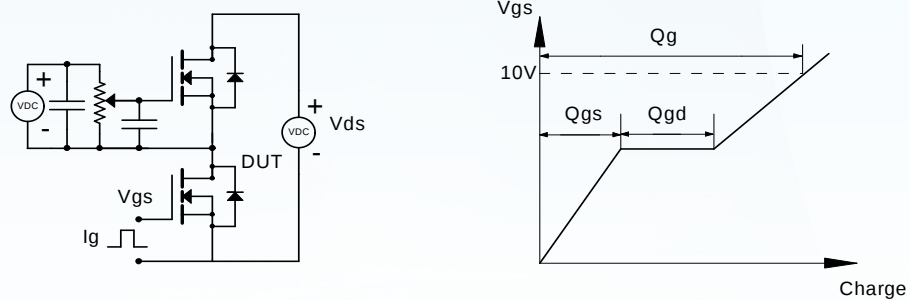


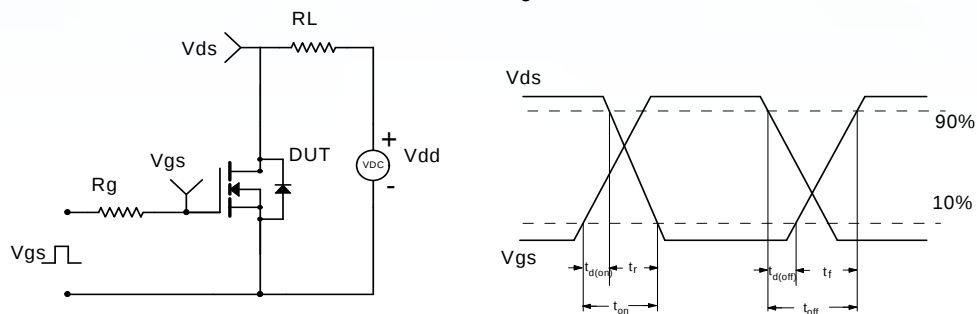
Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)

Dual N-Channel MOSFET

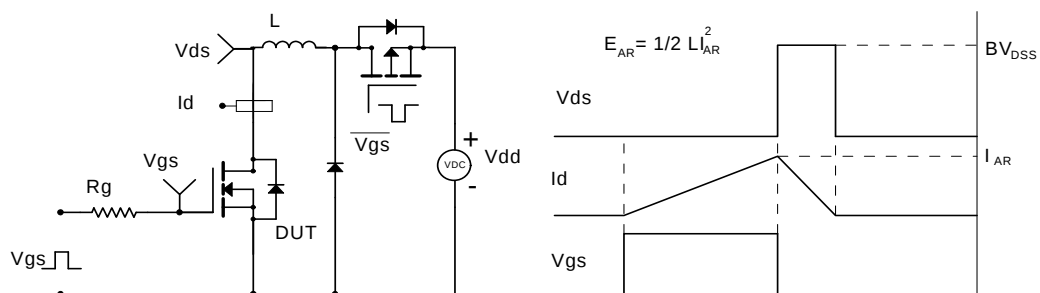
Gate Charge Test Circuit & Waveform



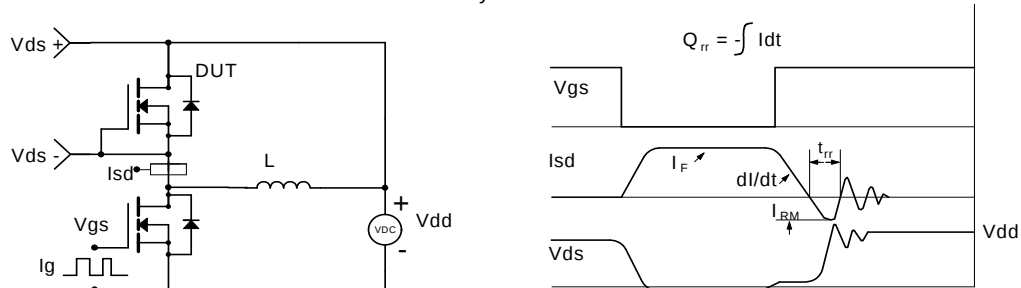
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



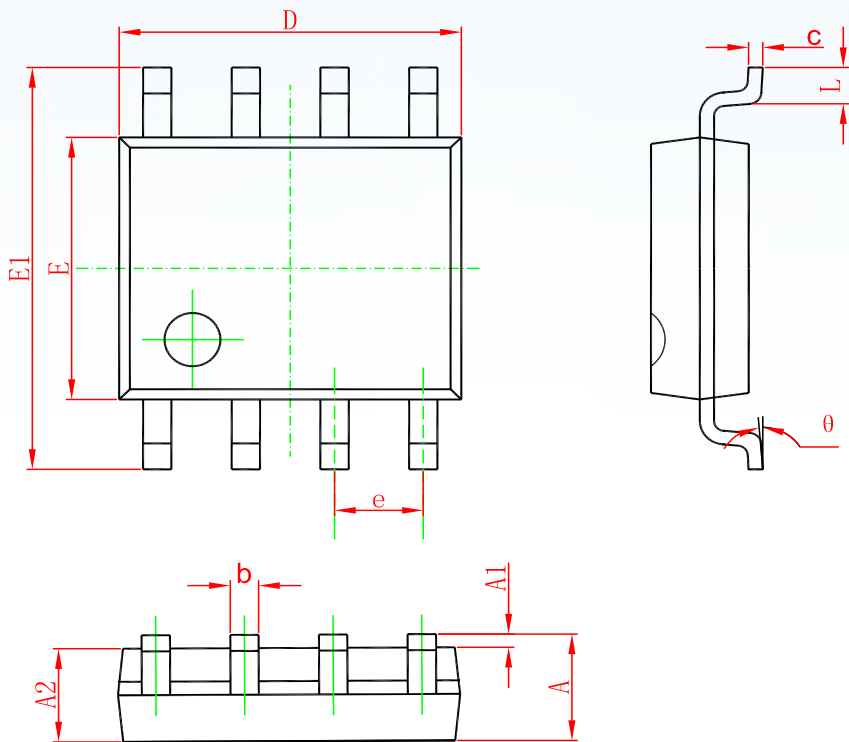
Diode Recovery Test Circuit & Waveforms



PACKAGE OUTLINE DIMENSIONS

Dual N-Channel MOSFET

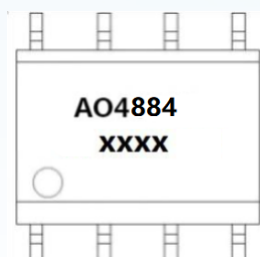
SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Dual N-Channel MOSFET

Marking



("XXXX"代表年份周期)

Ordering information

Order code	Package	Baseqty	Deliverymode
AO4884	SOP-8	3000	Tape and reel

Disclaimer

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